Abstracts

MESFET Linearity Improvement by Channel Doping Control

J.C. Pedro. "MESFET Linearity Improvement by Channel Doping Control." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1527-1530.

The present work is intended to evaluate the linearity that can be provided by general purpose MESFETS. By a simple physics-based analysis, and a practical amplifier design, it will be proved that educated device and bias point selection, can approximate IMD performance of normal channel doping profiles, to the one that expected from a MESFET device with a specially tailored doping profile.

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